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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.	
10/685,790	10/16/2003	Hirofumi Watatani	032015	7016	
38834 7.	90 05/18/2005		EXAMINER		
WESTERMAN, HATTORI, DANIELS & ADRIAN, LLP 1250 CONNECTICUT AVENUE, NW SUITE 700 WASHINGTON, DC 20036			CHEN, KI	CHEN, KIN CHAN	
			ART UNIT	PAPER NUMBER	
			1765		
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DATE MAILED: 05/18/2005

Please find below and/or attached an Office communication concerning this application or proceeding.

VIX

Application/Control Number: 10/685,790

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DETAILED ACTION

Claim Rejections - 35 USC § 103

- 1. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:
 - (a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.
- 2. Claims 1-10 are rejected under 35 U.S.C. 103(a) as being unpatentable over admitted prior art in view of Liu et al (US 6,117,345; hereinafter "Liu").

In a method for semiconductor device fabrication, the admitted prior art (page 3 of the specification; Fig. 4B) teaches that an interlayer insulating film may be formed on a surface of a substrate having an insulating surface, formed with semiconductor elements, and having a conductive member exposed in a area of the insulating surface. A first antireflection film may be formed on a surface of an underlying substrate. The first antireflection film may suppression reflection in an absorption mode. A second antireflection film may be formed on the first antireflection film. The second antireflection film may suppress reflection in a countervailing interference mode. A photosensitive resist film may be formed thereon. A latent image may be formed in the photosensitive resist film by exposing the photosensitive resist film to light having a first wavelength. The exposed photosensitive resist film may be

developed to form an opening through the first photosensitive resist. The interlayer insulating film may be etched by using the first photosensitive resist film as a mask.

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Unlike the claimed invention, the admitted prior art does not teach a cap film may be formed on the second antireflection film. In the method for forming wiring structure, Liu teaches that a cap layer may be formed over an antireflection layer (so-called protective layer in Liu) for the purpose of absorbing the light, col. 7, lines11-16, 19-21, and 64-65. The cap layer may serve as a hardmask as well as a second antireflection layer which created destructive interference to prevent light from reflecting (col. 7, lines 58-67). The cap layer may be used to reduce the contamination when the photoresist is removed (col. 8, lines 33-47). Hence, it would have been obvious to one with ordinary skill in the art to use the cap layer as disclosed by Liu in the process of admitted prior art because Liu teaches that to do so would reduce the contamination when the photoresist is removed.

Dependent claims 2-5 and 7-10 differ from the combined prior art by specifying various attenuation coefficients of cap film, first antireflection film, and second antireflection film. However, since the combined prior art has the same functions and serves same purposes (such as reducing the contamination while removing the photoresist, suppression reflection in an absorption mode, suppression reflection in an interference mode), it would have been obvious to one with ordinary skill in the art to adjust various attenuation coefficients of cap film, first antireflection film, and second film because same are merely a matter of choices of design depending on the specific product requirements.

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Allowable Subject Matter

3. Claims 11-15 are allowed.

The following is an examiner's statement of reasons for allowance:

The references of record do not teach or suggest a method comprising:

Removing the first photosensitive resist film; forming a second photosensitive resist film on the cap film; forming an opening through the second photosensitive resist, the opening corresponding to the wiring pattern to be formed on the interlayer insulating film, etching the interlayer insulating film to form a wiring groove by using the second photosensitive resist film as a mask.

4. Any inquiry concerning this communication or earlier communications from the examiner should be directed to Kin-Chan Chen whose telephone number is (571) 272-1461. If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Nadine Norton can be reached on (571) 272-1465. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306. Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you

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have questions on access to the Private PAIR system, contact the Electronic Business

Center (EBC) at 866-217-9197 (toll-free).

May 12, 2005

Kin-Chan Chen **Primary Examiner**

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